



6N90-C

Power MOSFET

6.0A, 900V N-CHANNEL POWER MOSFET

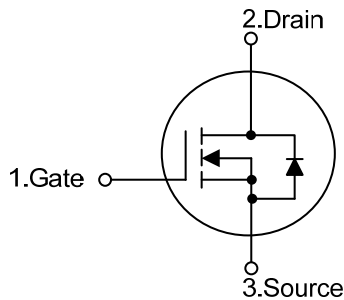
DESCRIPTION

The UTC **6N90-C** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} \leq 2.3 \Omega$ @ $V_{GS}=10V$, $I_D=3.0A$
- * Low Reverse Transfer Capacitance
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

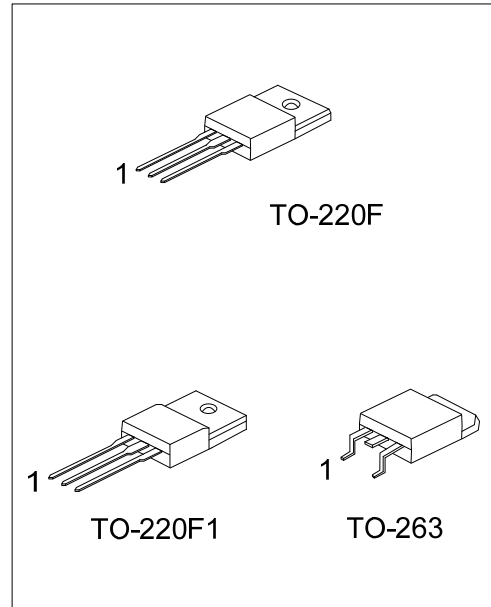


ORDERING INFORMATION

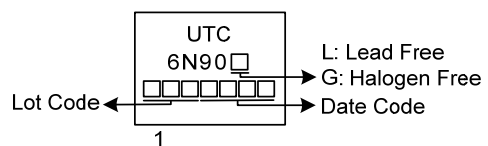
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N90L-TF1-T	6N90G-TF1-T	TO-220F1	G	D	S	Tube
6N90L-TF3-T	6N90G-TF3-T	TO-220F	G	D	S	Tube
6N90L-TQ2-T	6N90G-TQ2-T	TO-263	G	C	E	Tube
6N90L-TQ2-R	6N90G-TQ2-R	TO-263	G	C	E	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

6N90G-TF1-T	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TF3: TO-220F, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	900	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	6	A
	Pulsed (Note 2)	I _{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	360	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
MOSFET dv/dt Ruggedness			50	V/ns
Power Dissipation	TO-220F/TO-220F1	P _D	40	W
	TO-263		124	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=10\text{mH}$, $I_{AS}=8.5\text{A}$, $V_{DD}=90\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 6.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	2.5	$^{\circ}\text{C}/\text{W}$
	TO-263		1	$^{\circ}\text{C}/\text{W}$

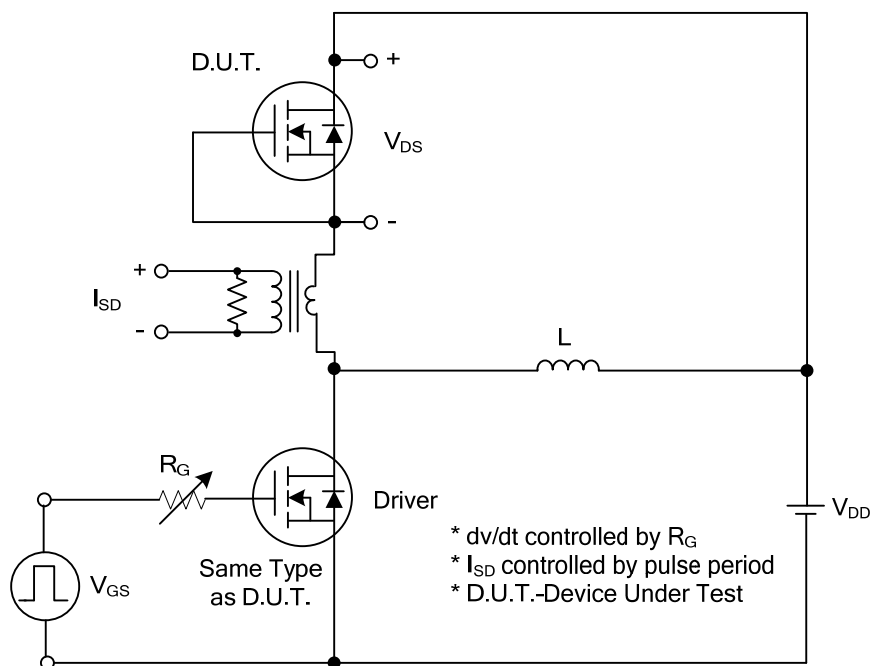
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	900			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=900V, V_{GS}=0V$			10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3.0A$			2.3	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		1000		pF
Output Capacitance	C_{OSS}			110		pF
Reverse Transfer Capacitance	C_{RSS}			11		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=100V, V_{GS}=10V, I_D=6A$ (Note 1, 2)		27		nC
Gate-Source Charge	Q_{GS}			7.2		nC
Gate-Drain Charge	Q_{GD}			6.2		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=100V, V_{GS}=10V, I_D=6A,$ $R_G=25\Omega$ (Note 1, 2)		20		ns
Turn-On Rise Time	t_R			18		ns
Turn-Off Delay Time	$t_{D(OFF)}$			80		ns
Turn-Off Fall Time	t_F			38		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				6	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				12	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=6.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=6.0A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$		880		nS
Body Diode Reverse Recovery Charge	Q_{rr}			6.4		μC

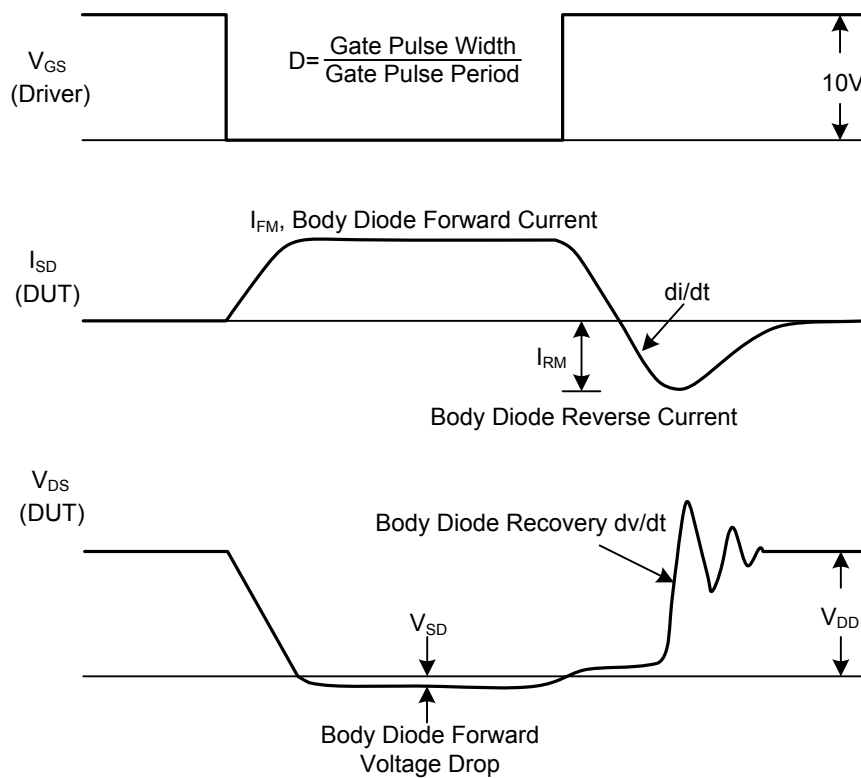
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

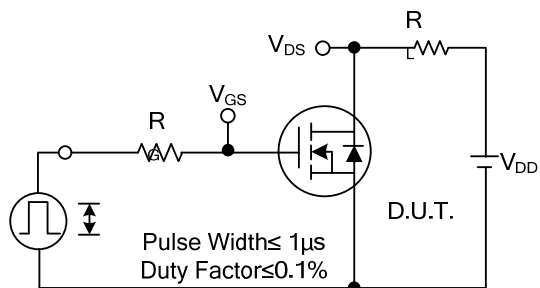


Peak Diode Recovery dv/dt Test Circuit

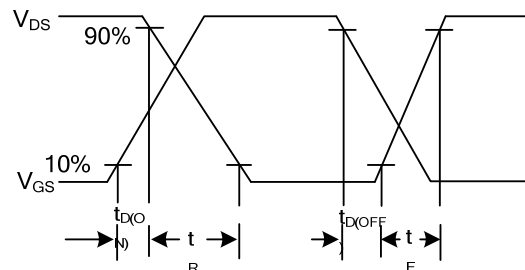


Peak Diode Recovery dv/dt Waveforms

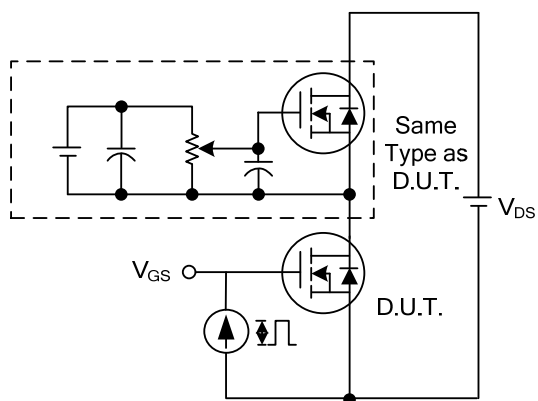
■ TEST CIRCUITS AND WAVEFORMS



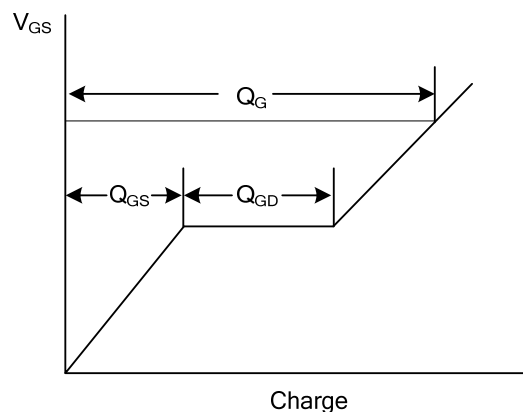
Switching Test Circuit



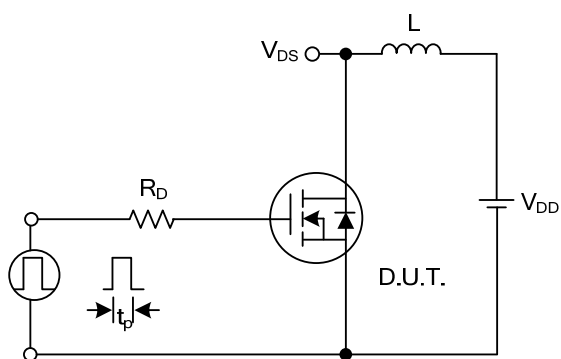
Switching Waveforms



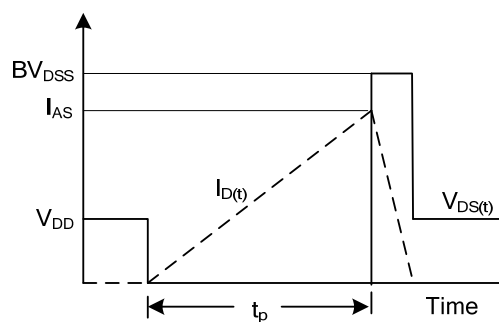
Gate Charge Test Circuit



Gate Charge Waveform

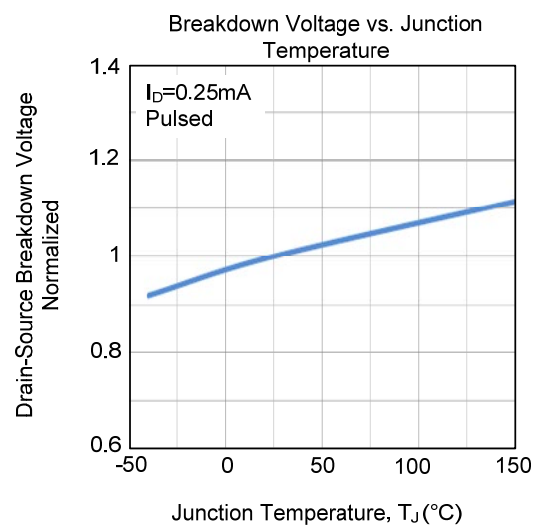
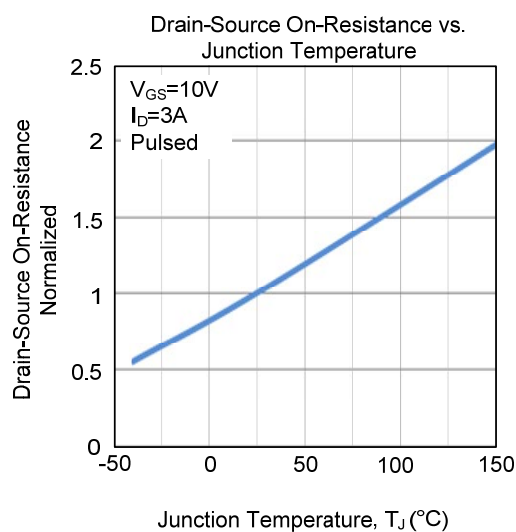
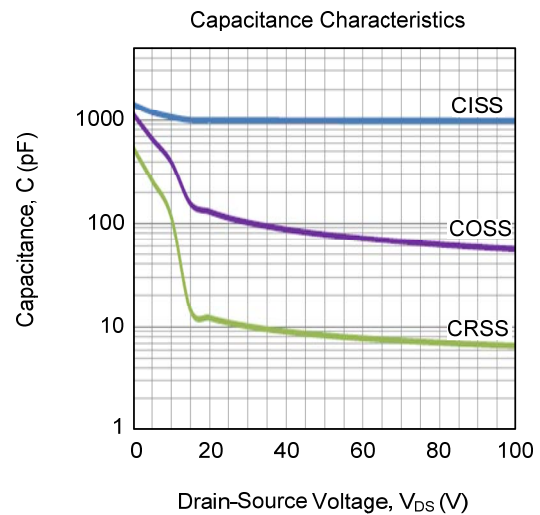
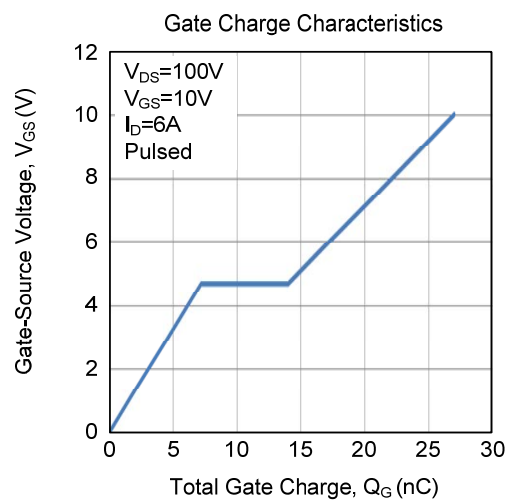
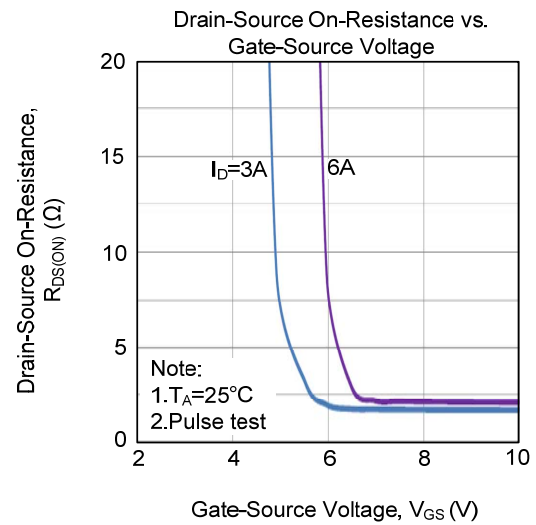
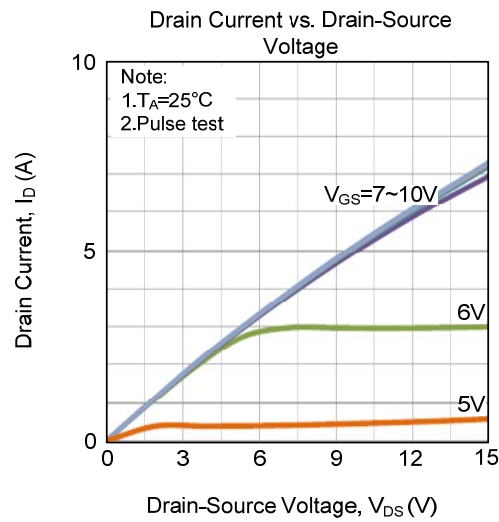


Unclamped Inductive Switching Test Circuit

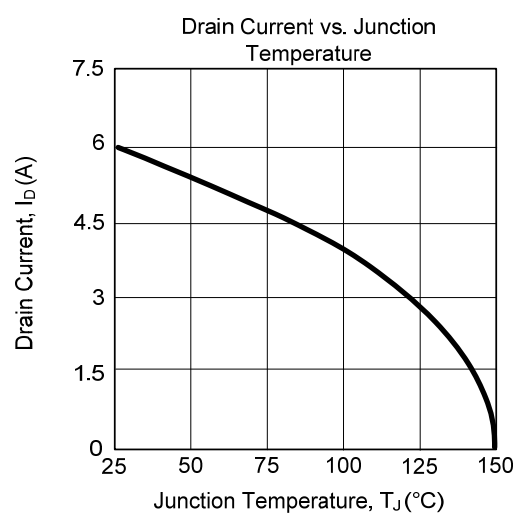
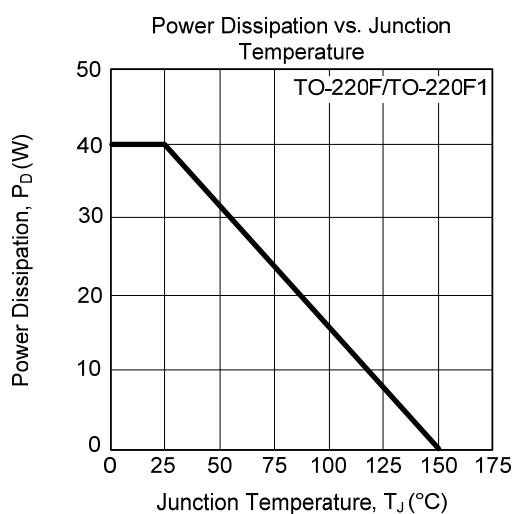
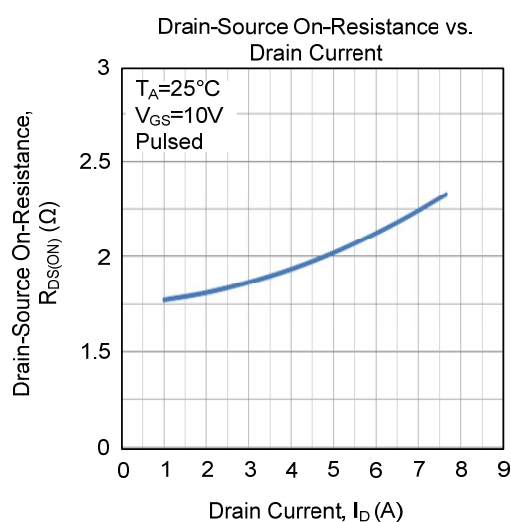
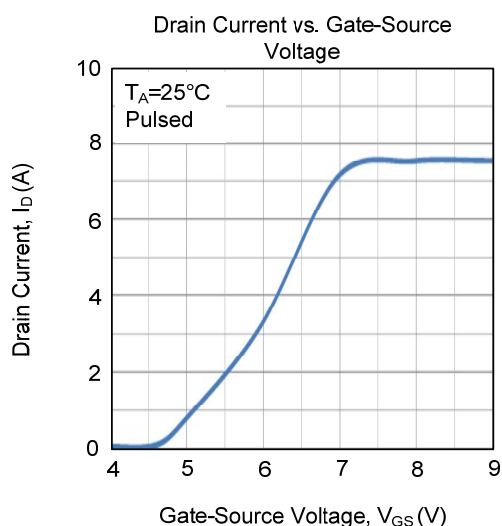
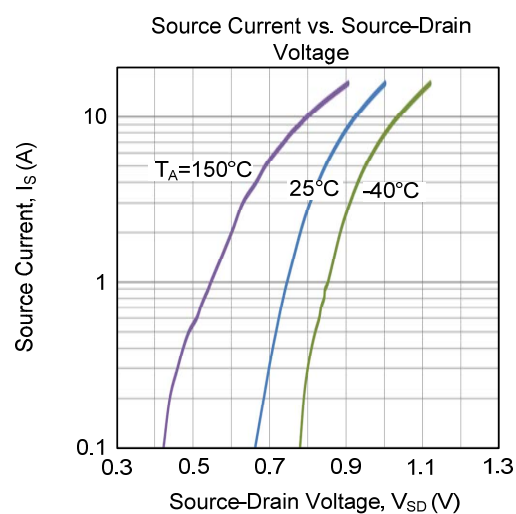
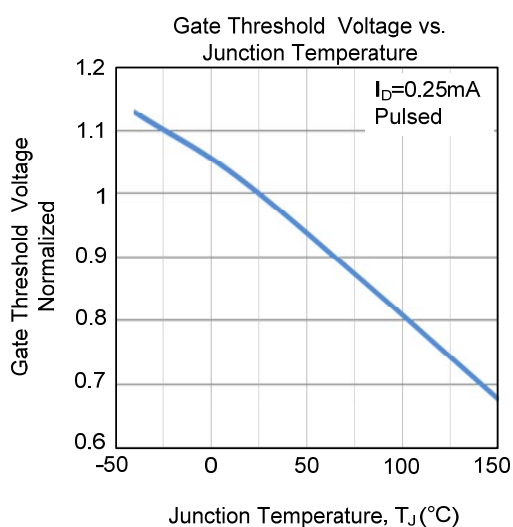


Unclamped Inductive Switching Waveforms

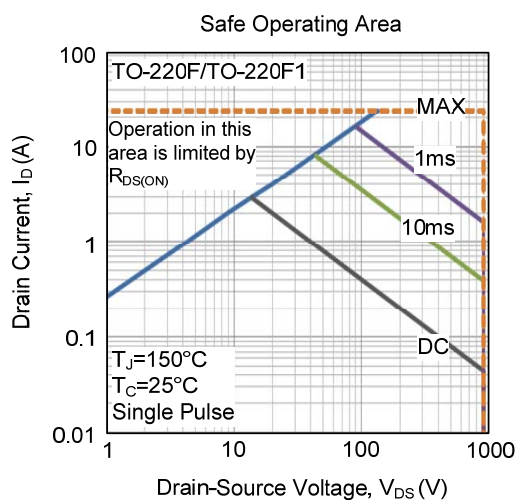
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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